

MBR16100CTG

Switch-mode Power Rectifier

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- Low Stored Charge Majority Carrier Conduction
- 16 A Total (8.0 A Per Diode Leg)
- This Device is Pb-Free and is RoHS Compliant*

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

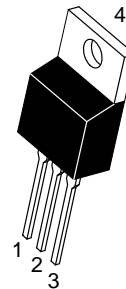
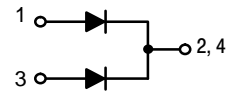
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B
Machine Model = C



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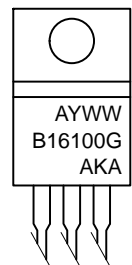
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SCHOTTKY BARRIER RECTIFIER 16 AMPERES, 100 VOLTS



**TO-220
CASE 221A
STYLE 6**

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
B16100 = Device Code
G = Pb-Free Package
AKA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
MBR16100CTG	TO-220 (Pb-Free)	50 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR16100CTG

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current ($T_C = 166^\circ\text{C}$) Per Diode Per Device	$I_{F(AV)}$	8.0 16	A
Peak Repetitive Forward Current (Square Wave, 20 kHz) $T_C = 165^\circ\text{C}$	I_{FRM}	16	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz)	I_{RRM}	0.5	A
Operating Junction Temperature (Note 1)	T_J	-65 to +175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case (Min. Pad) Junction-to-Ambient (Min. Pad)	$R_{\theta JC}$ $R_{\theta JA}$	2.0 60	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Min	Typical	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 8.0\text{ A}$, $T_J = 125^\circ\text{C}$) ($i_F = 8.0\text{ A}$, $T_J = 25^\circ\text{C}$) ($i_F = 16\text{ A}$, $T_J = 125^\circ\text{C}$) ($i_F = 16\text{ A}$, $T_J = 25^\circ\text{C}$)	V_F	-	0.56 0.68 0.67 0.79	0.60 0.74 0.69 0.84	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$)	i_R	-	0.95 0.0013	5.0 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

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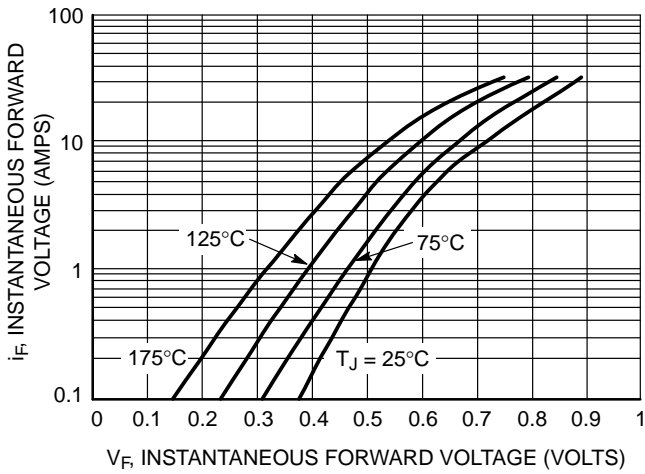


Figure 1. Typical Forward Voltage Per Diode

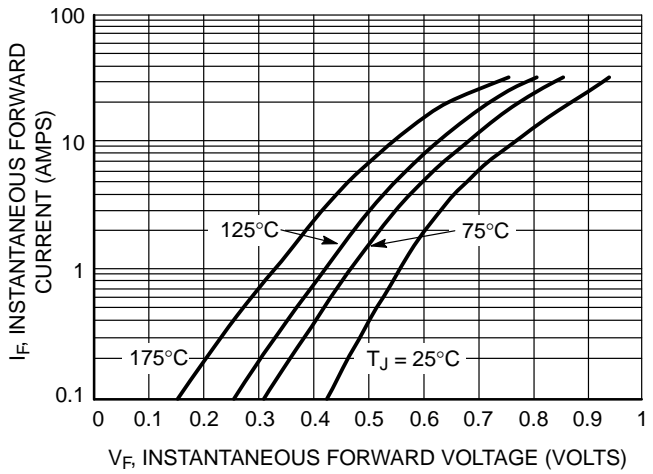


Figure 2. Maximum Forward Voltage Per Diode

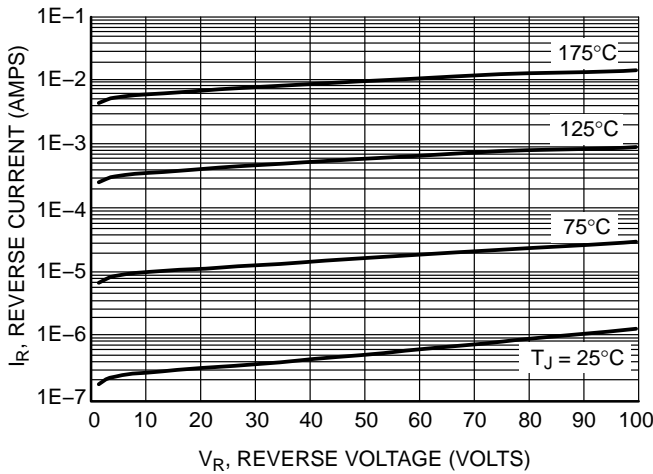


Figure 3. Typical Reverse Current Per Diode

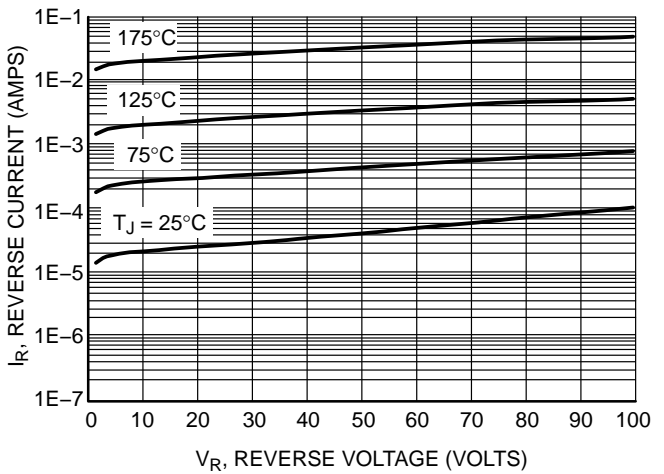


Figure 4. Typical Capacitance Per Diode

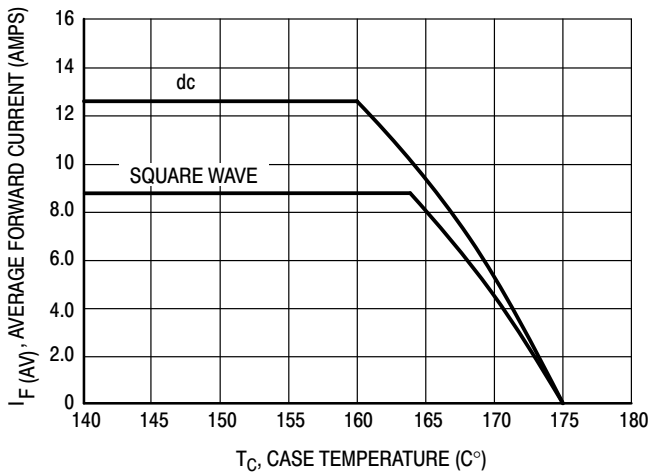


Figure 5. Current Derating, Case Per Leg

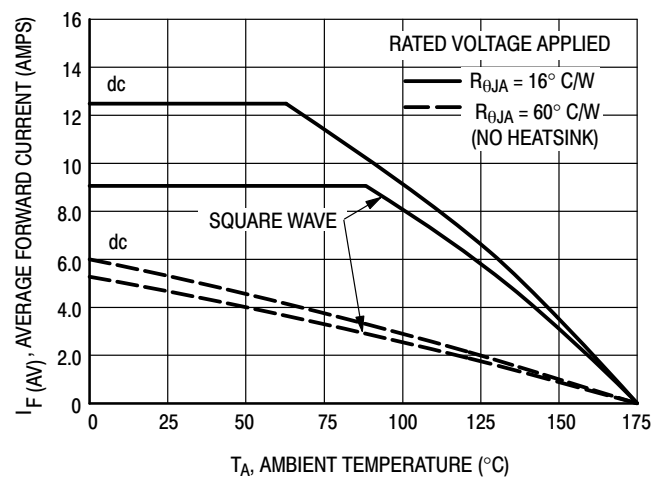


Figure 6. Current Derating, Ambient Per Leg

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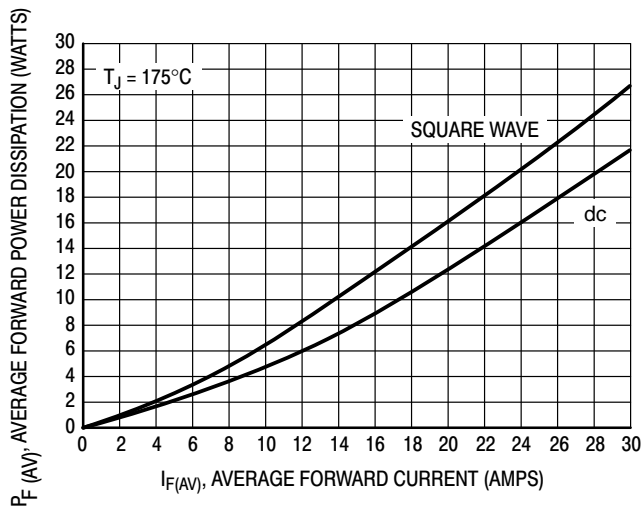


Figure 7. Forward Power Dissipation

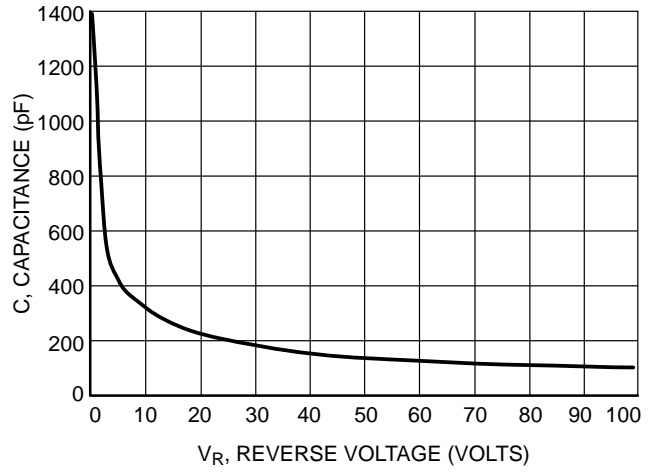
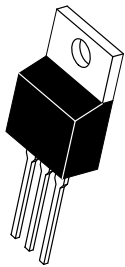


Figure 8. Typical Capacitance Per Diode

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

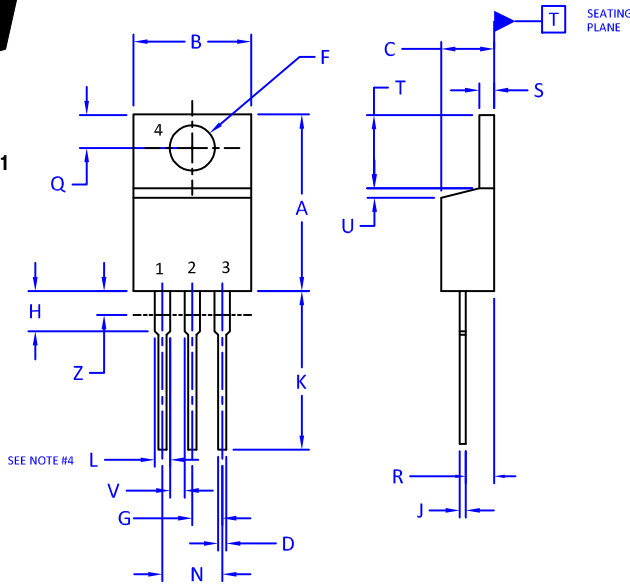
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SCALE 1:1

TO-220 CASE 221A-09 ISSUE AJ

DATE 05 NOV 2019



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 2:

- PIN 1. BASE
- 2. EMITTER
- 3. COLLECTOR
- 4. EMITTER

STYLE 3:

- PIN 1. CATHODE
- 2. ANODE
- 3. GATE
- 4. ANODE

STYLE 4:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

STYLE 5:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

STYLE 6:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

STYLE 7:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

STYLE 8:

- PIN 1. CATHODE
- 2. ANODE
- 3. EXTERNAL TRIP/DELAY
- 4. ANODE

STYLE 9:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 10:

- PIN 1. GATE
- 2. SOURCE
- 3. DRAIN
- 4. SOURCE

STYLE 11:

- PIN 1. DRAIN
- 2. SOURCE
- 3. GATE
- 4. SOURCE

STYLE 12:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. NOT CONNECTED

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